

ABSTRACT OF DISCLOSURE

A solid image capturing element comprising a plurality of vertical shift registers arranged to each correspond to a column
5 of a plurality of light receiving pixels in a matrix arrangement,
a horizontal shift register provided on an output side of the
plurality of vertical shift registers, and an output section
provided on an output side of the horizontal shift register. In
this solid image capturing element, a reverse conductive
10 semiconductor region is formed over one major surface of one
conductive semiconductor substrate, the plurality of light
receiving pixels, the plurality of vertical shift registers, the
horizontal shift register, and the output section are formed in
the semiconductor region, and a portion of the semiconductor region
15 where the output section is formed has a higher dopant concentration
than the portion of the semiconductor region where the horizontal
shift register is formed.